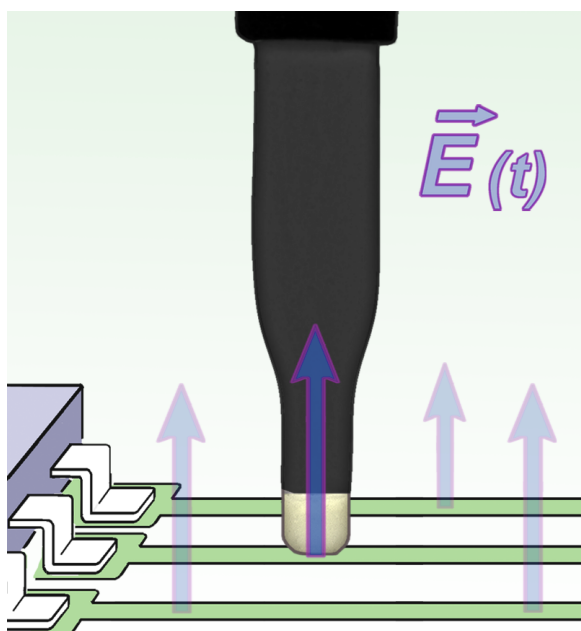


RF-E 10

E-Field Probe 30 MHz up to 3 GHz

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Short description

The electrode underneath the RF-E 10 probe head has a width of approx. 0.2 mm, which can locate even the smallest E-field sources, e.g. conducting paths with a width of 0.1 mm or, single IC pins at high pin ICs.

The RF-E 10 is a passive near-field probe. It has a higher resolution than the RF-E 02 and RF-E 05 probes. Because the probe head should be positioned directly onto the measuring object (high electrical field strength), it is not suitable for measurements within high-scale ranges. This can be done using RF-E 05 and RF-E 02. The E-field probe is small and handy. It has a current attenuating sheath and its upper side is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50 Ω input. The E-field probe does not have an internal terminating resistance of 50 Ω .

Technical parameters

Frequency range	30 MHz ... 3 GHz
Resolution	≈ 0.2 mm
Probe head dimensions	$\approx (0.5 \times 2)$ mm
Connector - output	SMB, male, jack
Weight	15 g

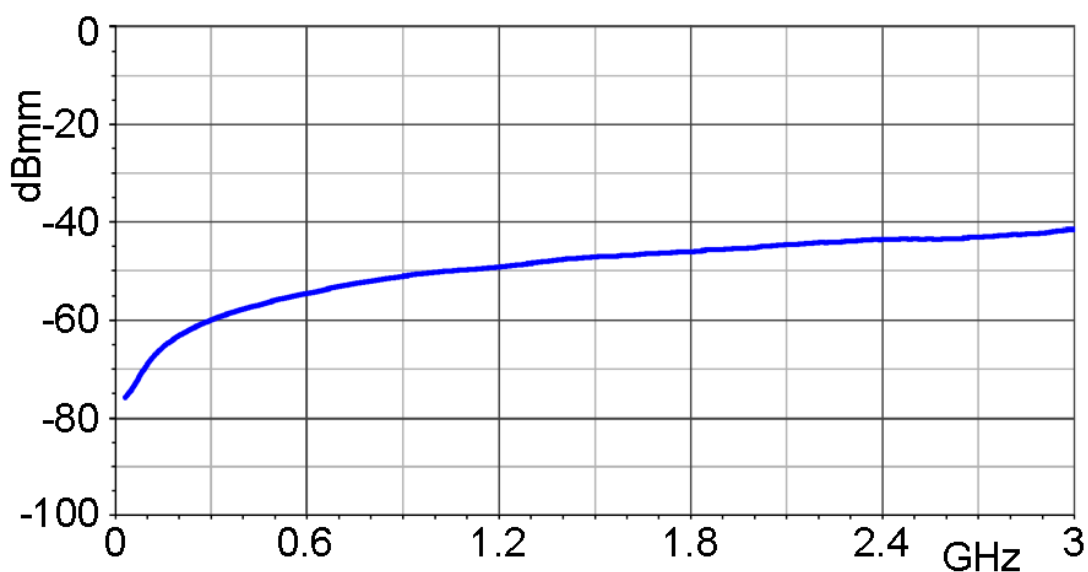


RF-E 10

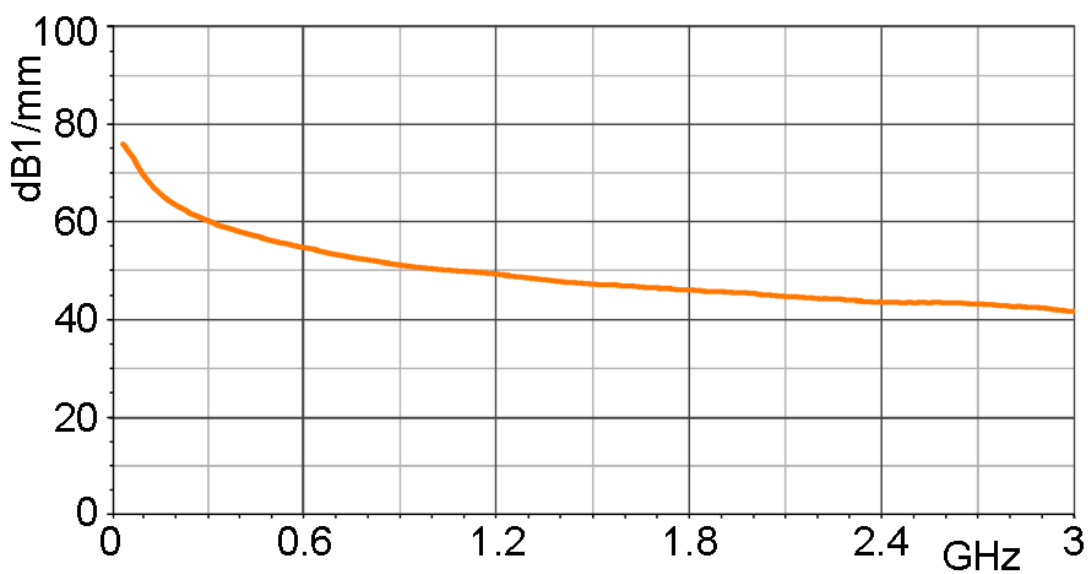
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Frequency response [dB μ V] / [dB μ V/mm]



E- field correction curve [dB μ V/mm] / [dB μ V]

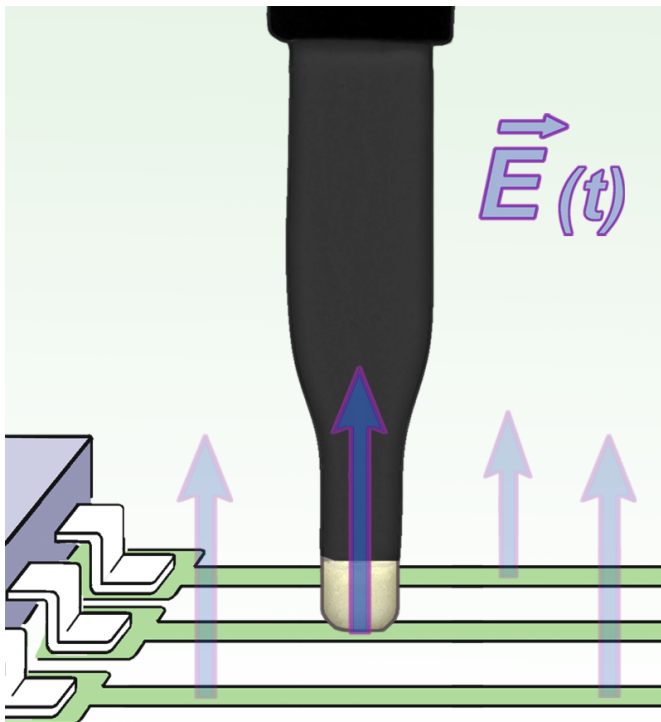


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Measuring principles



Probe head

